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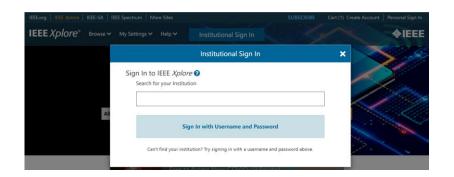


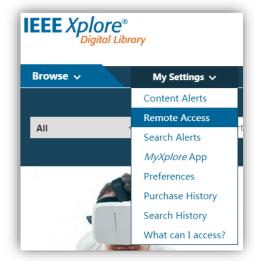


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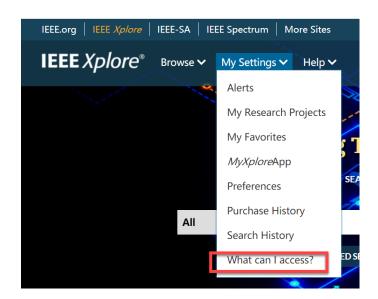






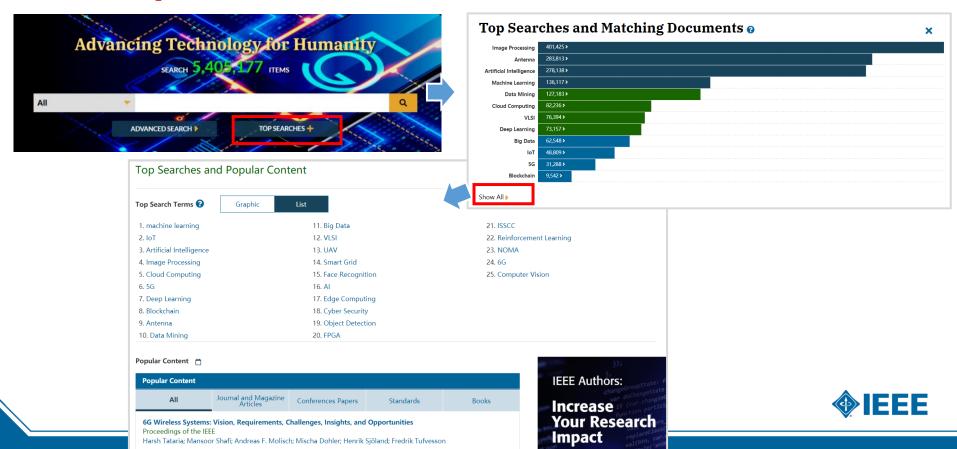
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Raymond W. Yeung

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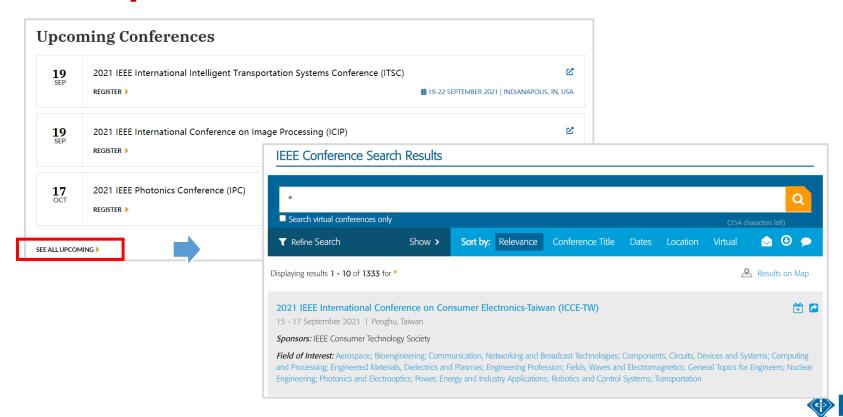
Raymond W. Yeung (Fellow, IEEE) was born in Hong Kong in June 1962. He received the B.S., M.Eng., and Ph.D. degrees in electrical engineering from Cornell University, Ithaca, NY, USA, in 1984, 1985, and 1988, respectively., He was on leave at the École Nationale Supérieure des Télécommunications, Paris, France, in Fall 1986, He was a Member of Technical Staff of AT&T Bell Laboratories from 1988 to 1991. Since 1991, he has been with The Chinese University of Hong Kong, where he is currently a Choh-Ming Li Professor of information engineering and the Co-Director of the Institute of Network Coding. He has held visiting positions at Cornell University, Nankai University, Bielefeld University, the University of Copenhagen, the Tokyo Institute of ... Show More



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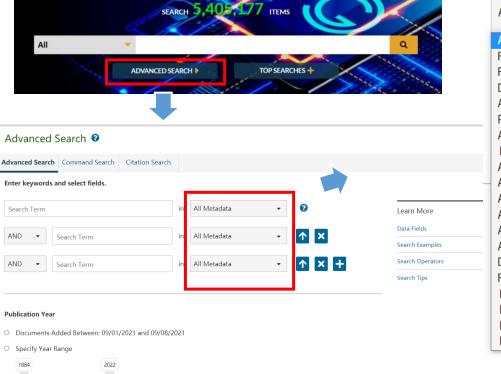


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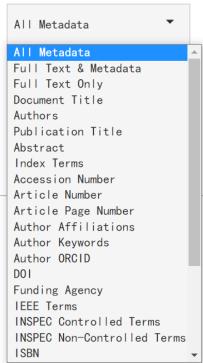
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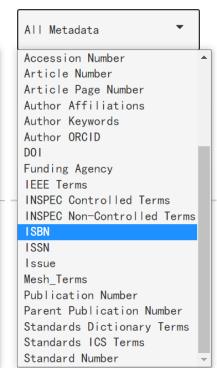


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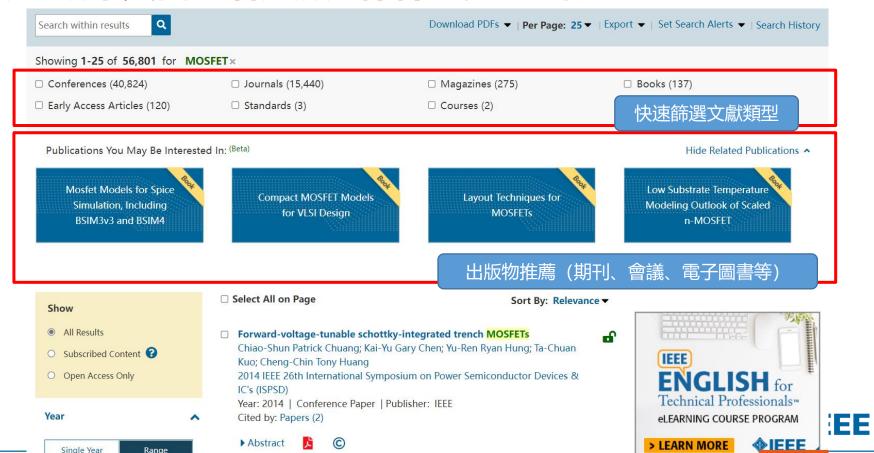






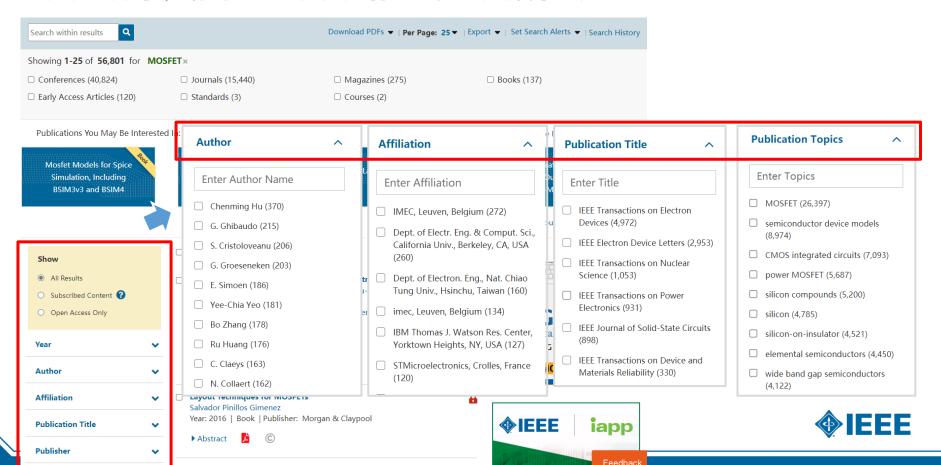
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Hybrid MOSFET/driver for ultra-fast switching



L. Tang: C. Burkhart

IEEE Transactions on Dielectrics and Electrical Insulation Year: 2009 | Volume: 16, Issue: 4 | Journal Article | Publisher: IEEI Cited by: Papers (8)

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The ultra-fast switching of power MOSFETs, in about 1 ns, is very challen

the parasitic inductance that is intrinsic to commercial packages used for Document Sections

drivers. Parasitic gate and source inductance not only limit the voltage r I. Introduction

internal gate structure but can also cause the gate voltage to oscillate. This paper describes a hybrid approach that substantially reduces the parasitic inductance between the driver and MOSFET gate, as well as between the MOSFET source and its external connection. A flip-chip assembly is used to directly attach a die-form power MOSFET and driver on a PCB. The parasitic inductances are significantly reduced by eliminating bond wires and minimizing lead length. The experimental results demonstrate ultra-fast switching of the power MOSFET with excellent control of the gate-source voltage.

Published in: IEEE Transactions on Dielectrics and Electrical Insulation (Volume: 16, Issue: 4, August 2009)

Page(s): 967 - 970

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SECTION I.

Introduction

Power MOSFETs have great potential as switches for high speed high voltage applications like pulsed power, the theoretical carrier transit time from drain to source is on the order of 200 ps in any cell of the silicon die [1]. Although the power MOSFET is

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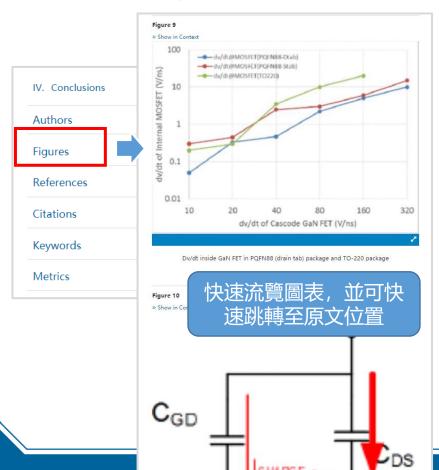
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MOSFET is the most popular semiconductor switch and has been widely used in power electronics systems, like power supply, PFC, etc. Recently, it is also used in cascode GaN FET [1], as shown in Figure 1. In order to achieve high efficiency, MOSFETs nowadays are designed with very low parasitic capacitances and inductances. Combined with well-designed PCB layout, MOSFETs switches at nano-seconds [2] [3]. However, GaN HEMT

2. "Application Advantages and Disadvantages of Modern Fast Switching MOSFETs in VRM", *PCIM Europe*, 2016.

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1. Can MOS

快速定位參考文獻

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of the semiconductor was proposed in [23], and was defined as:

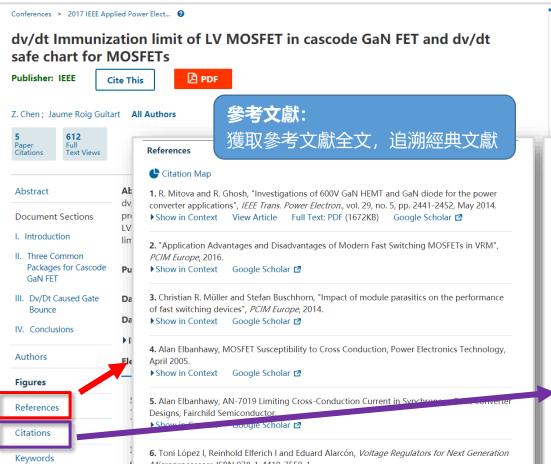
$$\sum_{\text{SC}} = \sum_{\text{chip}} + \sum_{\text{pack},x} = \left(\sum_{n} \sigma_{\text{chip},x(n)} A_{\text{chip},n}\right) + \sum_{\text{pack},x}$$
(1)

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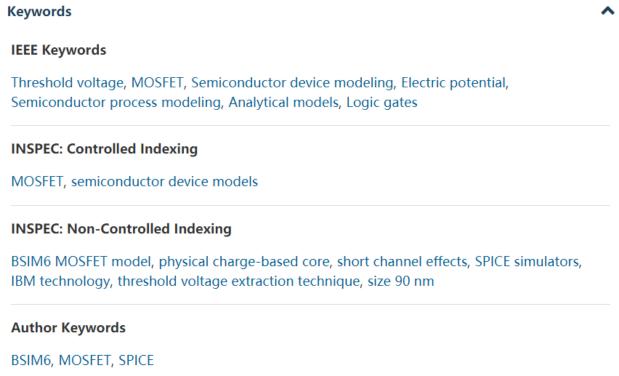
- 1. Masahiro Koyama, Kentaro Ikeda, Kazuto Takao, "Novel cascode GaN module integrated a single gate driver IC with high switching speed controllability", *Power Electronics and Applications (EPE'18 ECCE Europe) 2018 20th European Conference on*, pp. P.1-P.8, 2018. Show Article Full Text: PDF (2528KB) Google Scholar 2
- 2. Tianhua Zhu, Fang Zhuo, Feng Wang, Hailin Wang, Xiaoping Sun, Shuhuai Shi, Baohui Ma, "Quantitative Analysis and Suppression Strategies of Dv/dt Induced Turn-on of Cascode GaN FETs in Half-bridge Circuits", Wide Bandgap Power Devices and Applications in Asia (WiPDA Asia) 2018 1st Workshop on, pp. 130-134, 2018.

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- 3. Tianhua Zhu, Fang Zhuo, Fangzhou Zhao, Feng Wang, Tong Zhao, "Quantitative Model-Based False Turn-on Evaluation and Suppression for Cascode GaN Devices in Half-Bridge Applications", *Power Electronics IEEE Transactions on*, vol. 34, no. 10, pp. 10166-10179, 2019. Show Article Full Text: PDF (8243KB) Google Scholar 2
- 4. Jian Chen, Xiong Du, Quanming Luo, Xinyue Zhang, Pengju Sun, Lin Zhou, "A Review of Switching Oscillations of Wide Bandgap Semiconductor Devices", Power Electronics IEEE Transactions and Associations 2018, pp. 31310, 2310, 2310.

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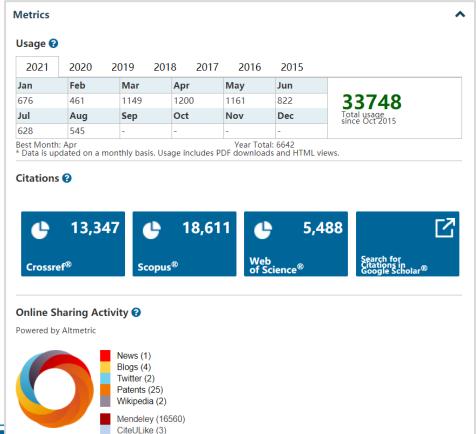






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Publication Topics

MOSFET, semiconductor device models, field effect transistors, technology CAD (electronics), silicon-on-insulator, ferroelectric materials, silicon, 1/f

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Chenming Hu (LF' 03) is currently a Distinguished Professor Emeritus with the University of California at Berkeley, Berkeley, CA, USA. He is also the Board Director of SanDisk Inc., San Jose, CA, USA, and Friends of Children with Special Needs, Fremont, CA, USA. He is known for his involvement in FinFET-the 3-D transistor, widely used IC reliability models, and BSIM-the industry standard transistor models used by most IC companies since 1997 to design CMOS products. (Based on document published on 29 August 2018).



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M. Abu-Rahma Amit Agarwal H. Agarwal Jong-Ho Bae Kaiman Chan

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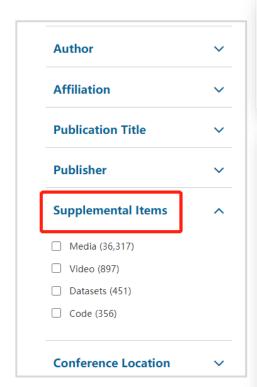
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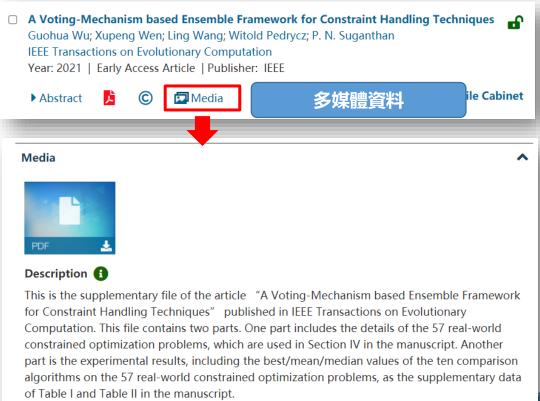
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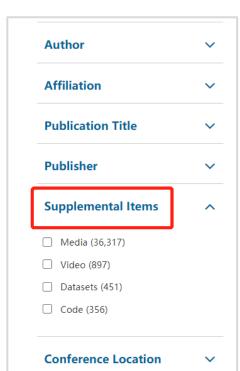
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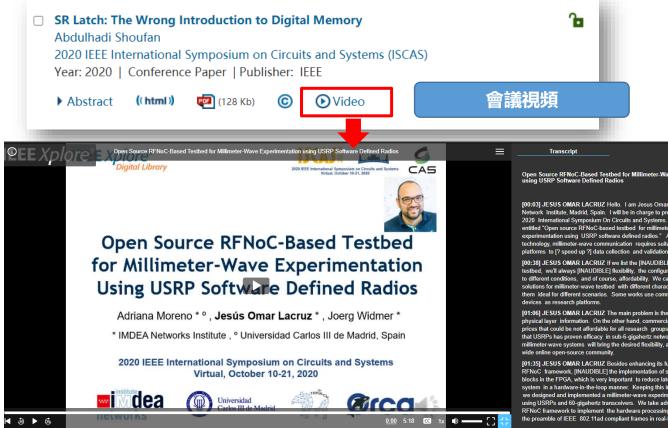
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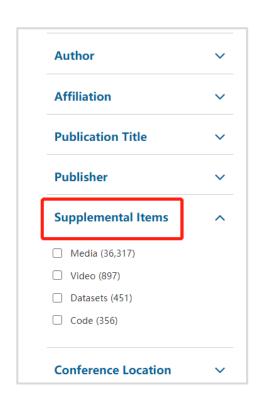


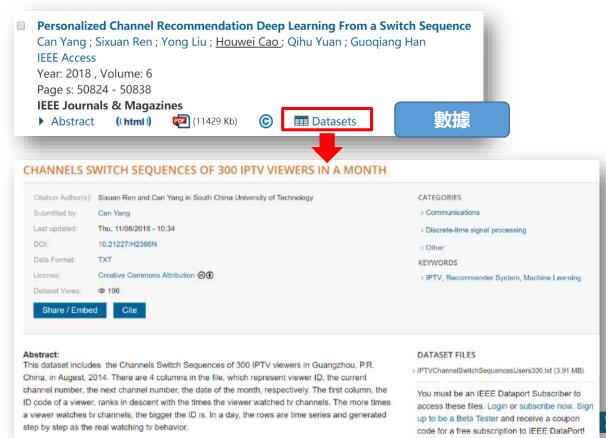


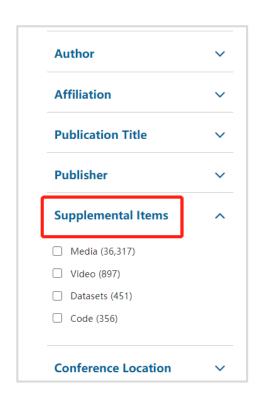


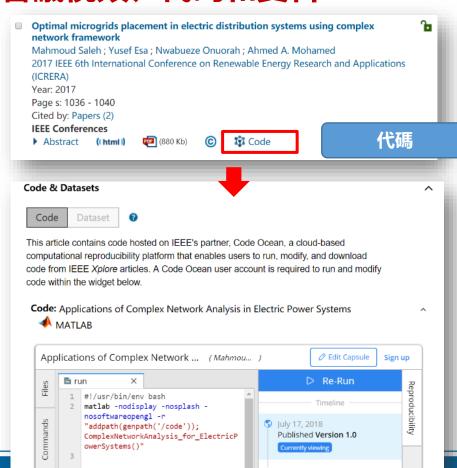






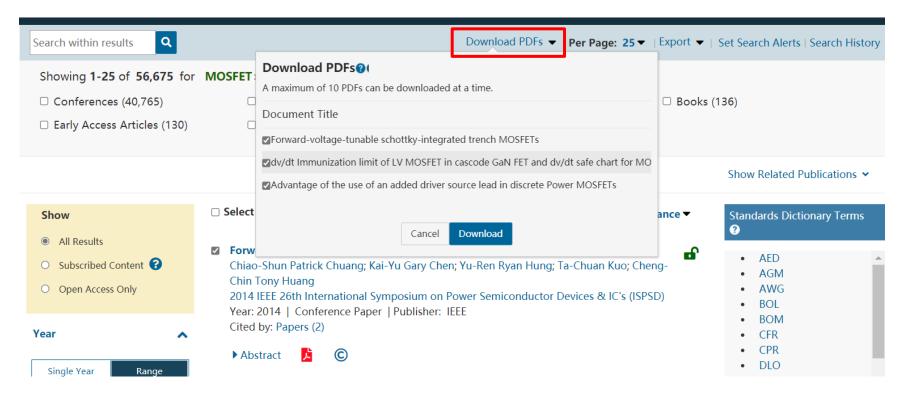






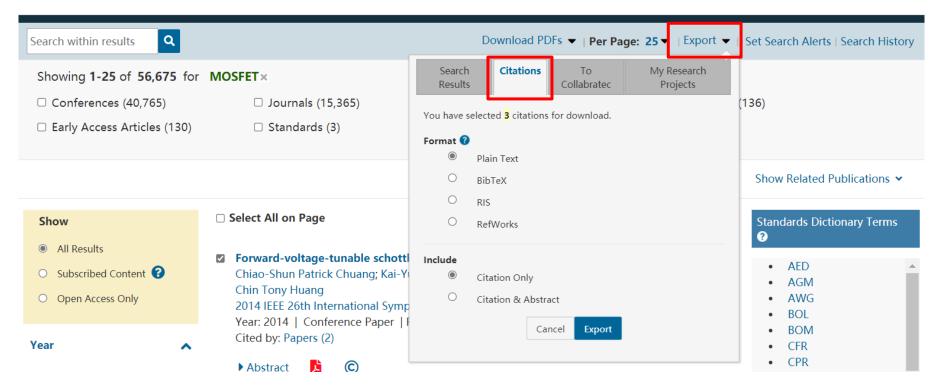


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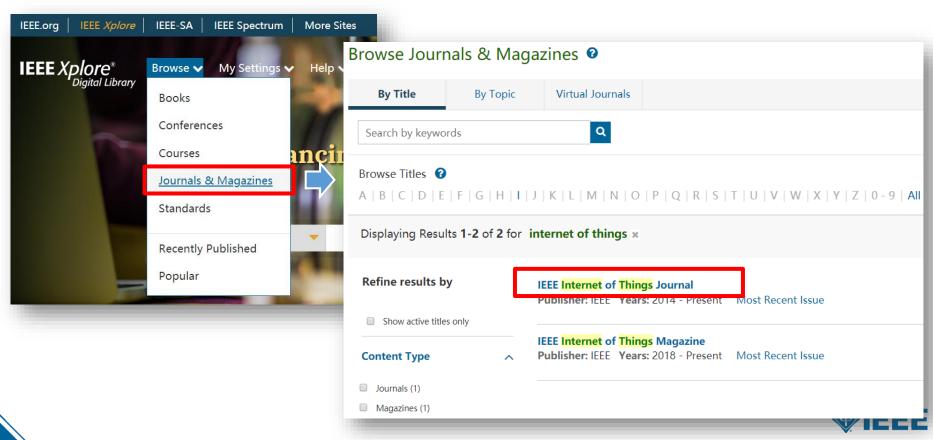


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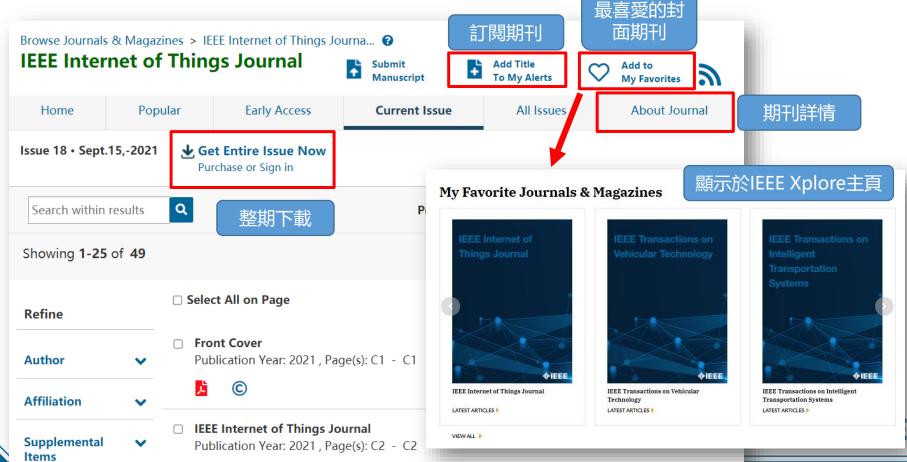


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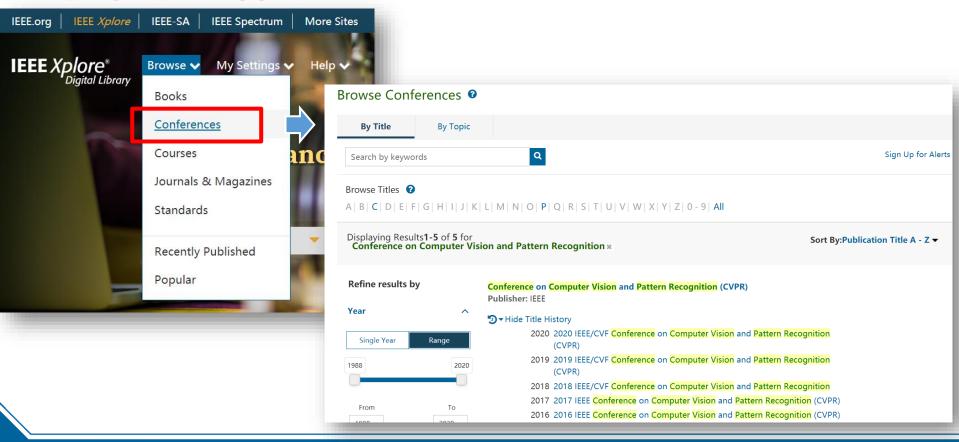


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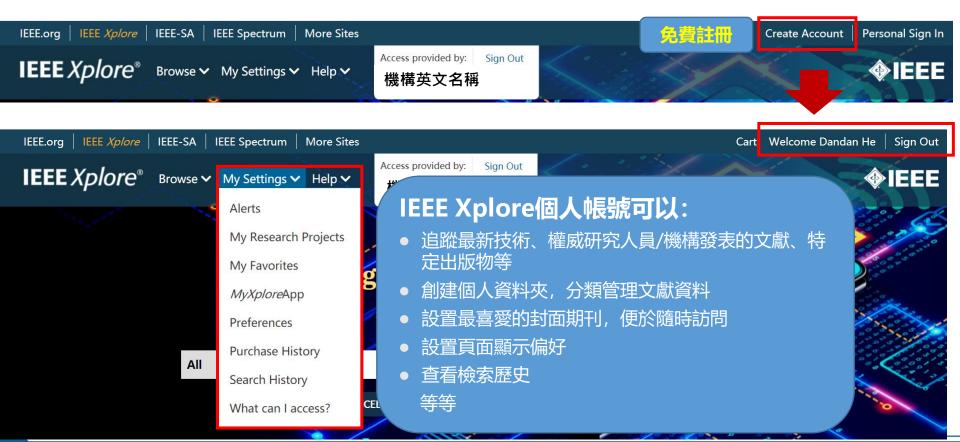
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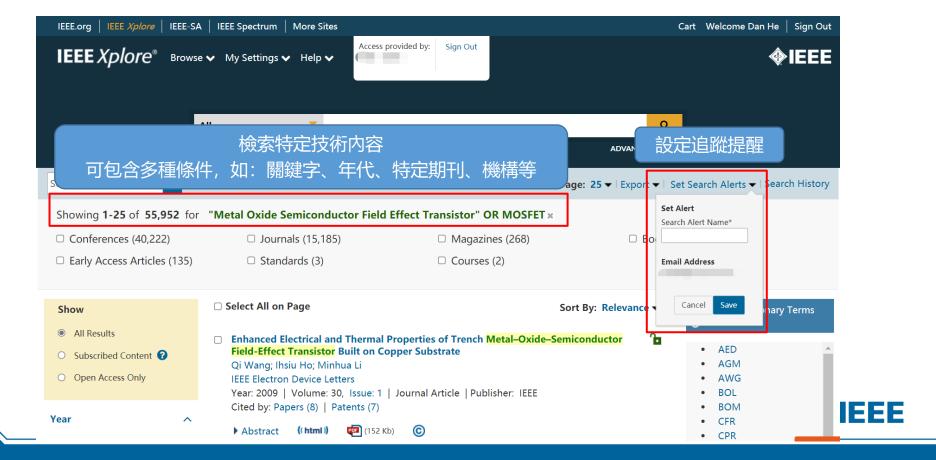
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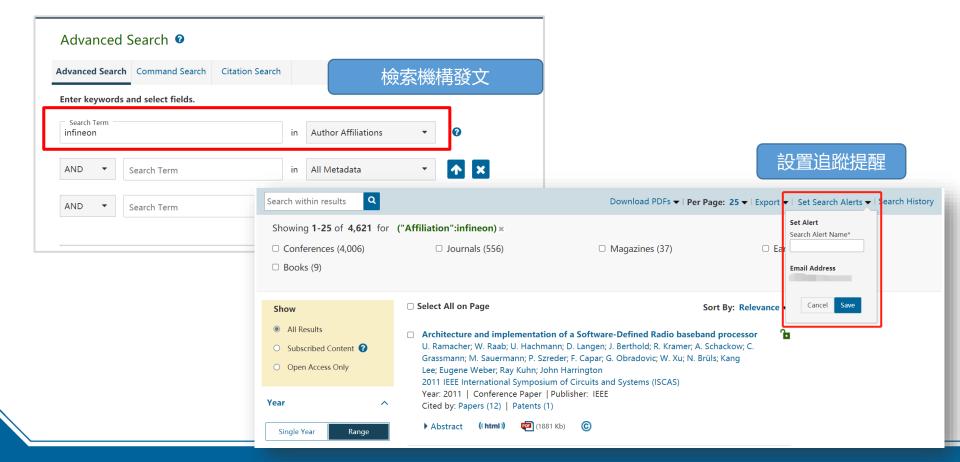
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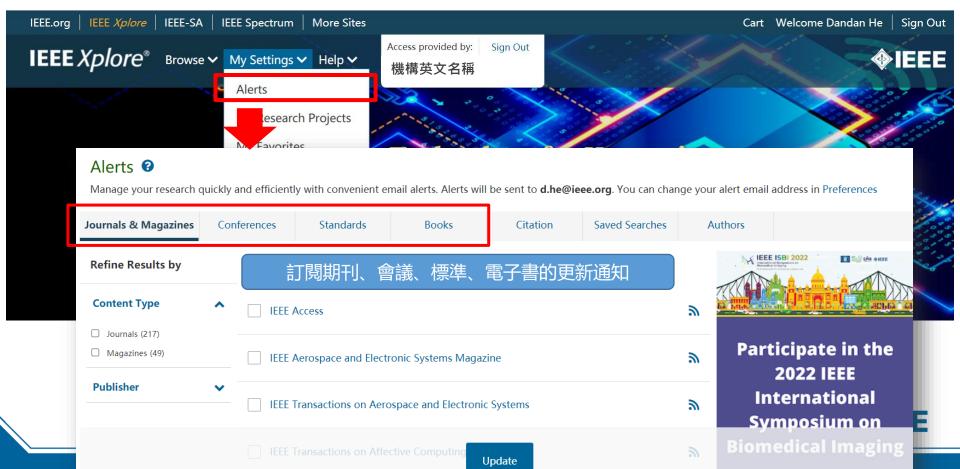
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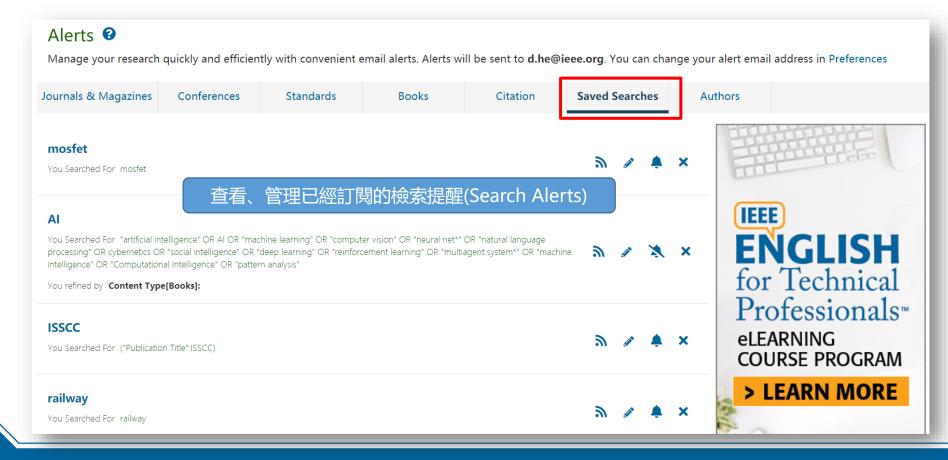
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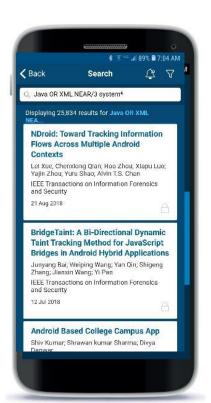
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